

Preliminary Specification: Subject to Change without Notice

N-Channel 80 V MOSFET

Product summary

V_{DS} (V)	$R_{DS(on),max}$ (m Ω)	I_D (A)
80	1.8 @ $V_{GS} = 10V$	215 ⁽¹⁾

Features

- For automotive applications and AEC-Q101 compliant
- Great FOM (figure of merit) with low $R_{DS(on)}$ SGT technology
- Fast switching speed
- 100% avalanche tested. High avalanche ruggedness.

Applications

- DC/DC conversion
- Power switch
- Motor drives

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Package and ordering information

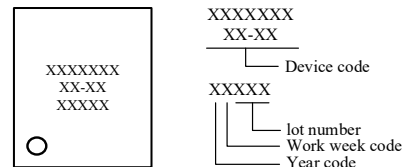
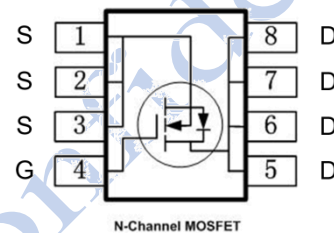
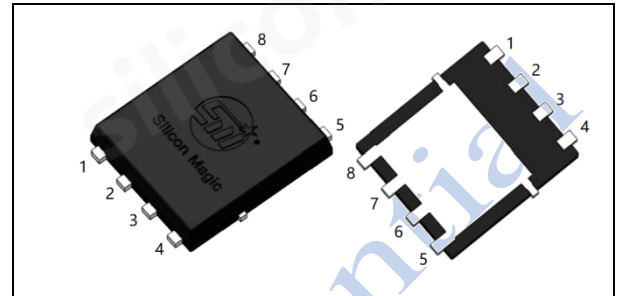
Ordering code	Package	Device code
SDA08N1P8CN-BA	PDFN5*6-8L	A08N1P8CN-BA

1. Maximum ratings

Absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DS}	80	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	$T_C = 25^\circ\text{C}$ ⁽¹⁾	215	A
	$T_C = 100^\circ\text{C}$	152	
	$T_A = 25^\circ\text{C}$ ⁽⁴⁾	28.9	
Pulsed drain current ⁽²⁾	$I_{D,pulse}$	862.4	
Avalanche energy, single pulse ⁽³⁾	E_{AS}	750	mJ
Power dissipation	$T_C = 25^\circ\text{C}$	166.6	W
	$T_A = 25^\circ\text{C}$ ⁽⁴⁾	3	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

PDFN5*6-8L



2. Thermal resistance ratings

Thermal resistance ratings				
Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	0.9	°C/W
Thermal resistance, junction-to-ambient ⁽⁴⁾	Steady state	$R_{\theta JA}$	50	

3. Electrical Characteristics

Electrical characteristics (T _J = 25°C unless otherwise noted)						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	80			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1 mA	2.2	3.0	3.8	V
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V			1	μA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 50 A		1.5	1.8	mΩ
Forward transconductance ⁽⁵⁾	g _{fs}	V _{DS} = 5 V, I _D = 50 A		146		S
Gate resistance	R _g	f = 1 MHz		1		Ω
Dynamic ⁽⁵⁾						
Total gate charge	Q _g	V _{DS} = 40 V, I _D = 50 A, V _{GS} = 10 V		59.5		nC
Gate-source charge	Q _{gs}			20.5		
Gate-drain charge	Q _{gd}			10.5		
Turn-on delay time	t _{d(on)}	V _{DS} = 40 V, I _D = 50 A, V _{GS} = 10 V, R _{GEN} = 1.6 Ω		13.6		ns
Rise time	t _r			12.0		
Turn-off delay time	t _{d(off)}			10.0		
Fall time	t _f			6.8		
Input capacitance	C _{iss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz		4314		pF
Output capacitance	C _{oss}			1361		
Reverse transfer capacitance	C _{rss}			33		
Reverse Diode Characteristics ⁽⁵⁾						
Diode forward voltage	V _{SD}	V _{GS} = 0 V, I _F = 50 A		0.8	1.1	V
Reverse recovery time	t _{rr}	V _{DS} = 40 V, I _F = 50 A, di/dt = 1000 A/μs		28		ns
Reverse recovery charge	Q _{rr}			226		nC

Notes

- (1) Package limited.
- (2) Pulse width limited by maximum junction temperature.
- (3) $V_{DS} = 40\text{ V}, V_{GS} = 10\text{ V}, L = 1\text{ mH}$.
- (4) $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5x1.5 in. board of FR-4 material.
- (5) Guaranteed by design, not subject to production testing.

4. Electrical characteristics diagrams

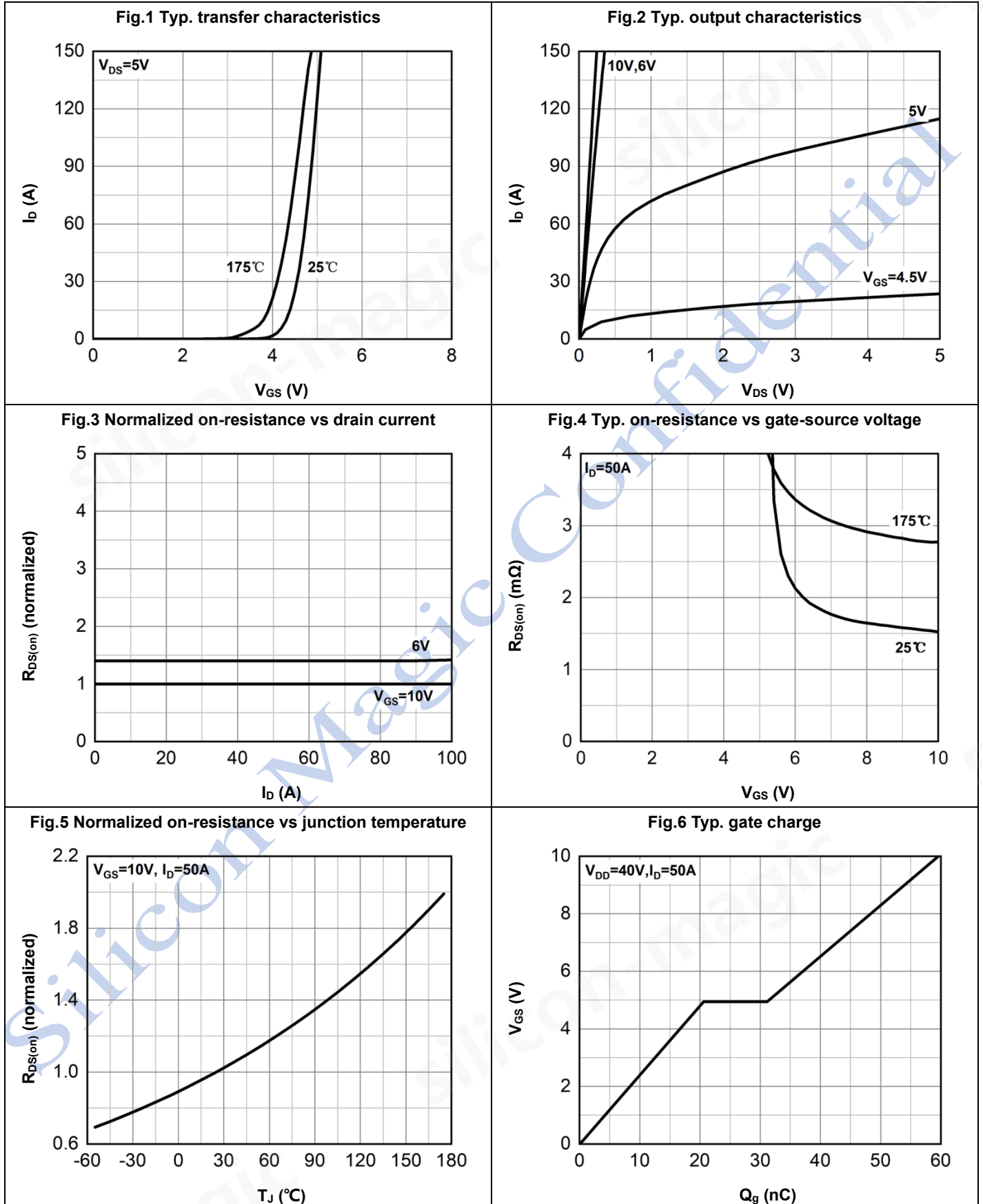


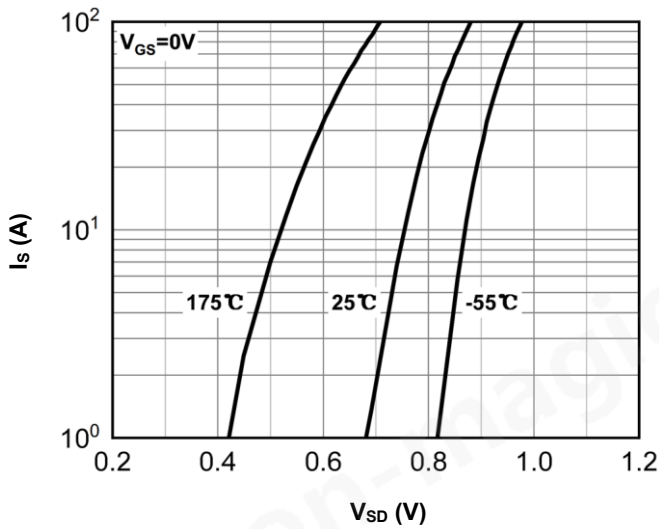
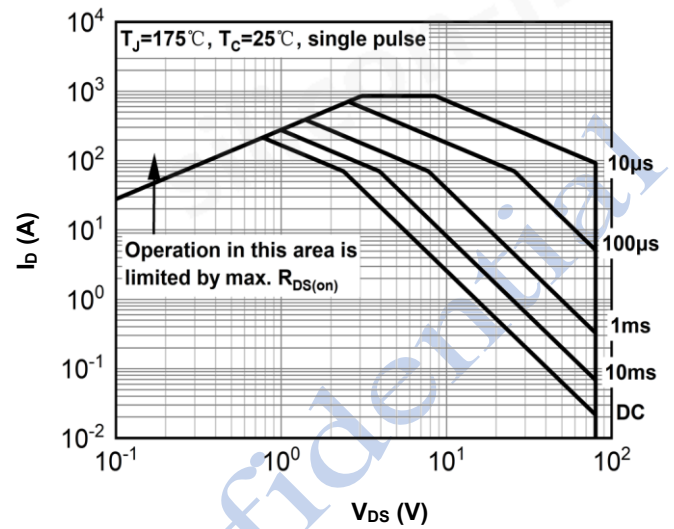
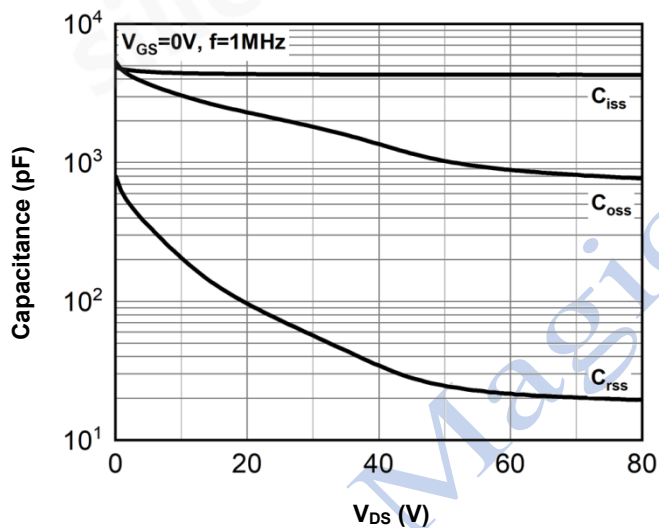
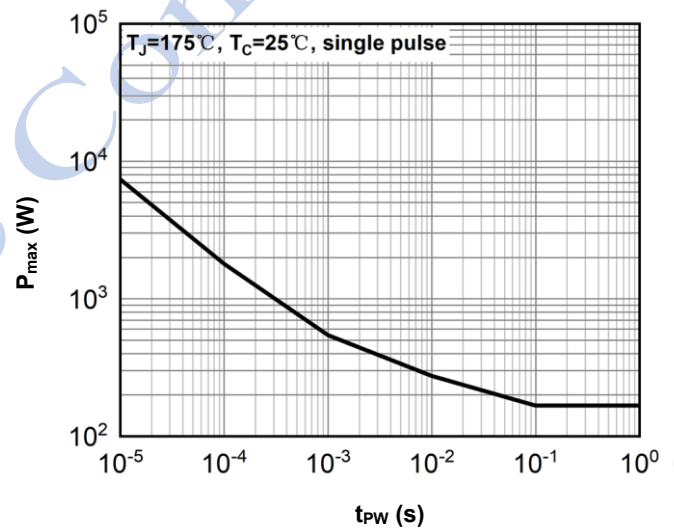
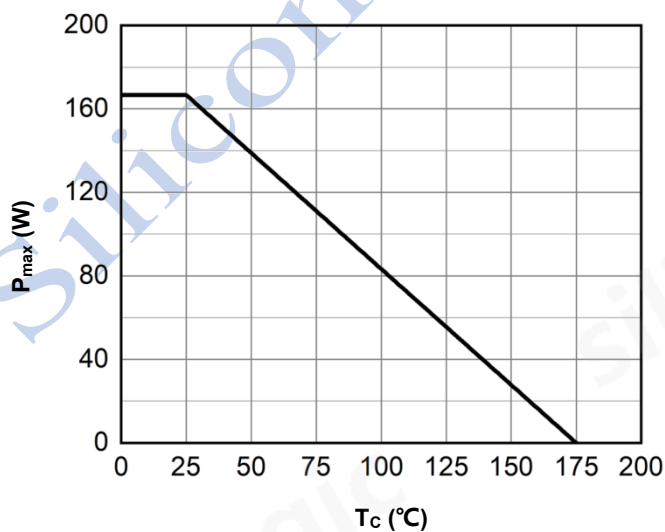
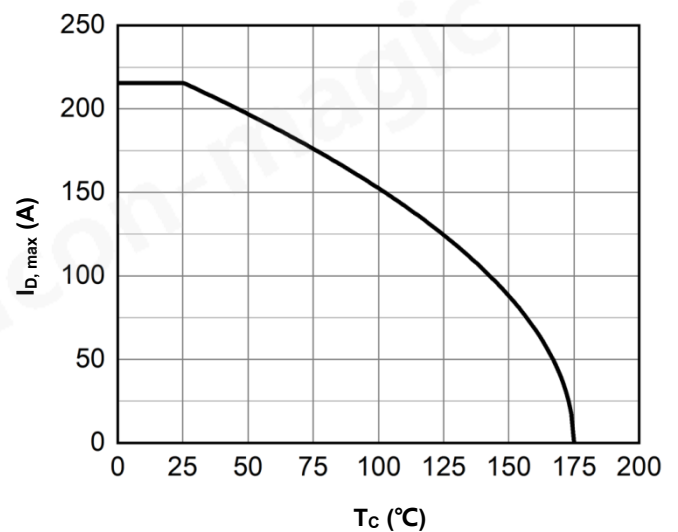
Fig.7 Typ. forward characteristics of body diode

Fig.8 Safe operating area

Fig.9 Typ. Capacitance

Fig.10 Single pulse maximum power dissipation

Fig.11 Max. power dissipation vs case temperature

Fig.12 Max. continuous drain current vs case temperature


Fig.13 Normalized $V_{(BR)DSS}$ vs junction temperature

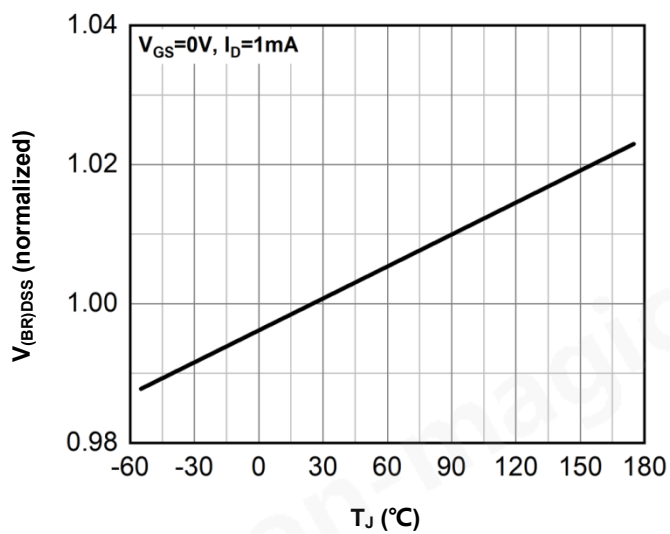


Fig.14 Normalized $V_{GS(th)}$ vs junction temperature

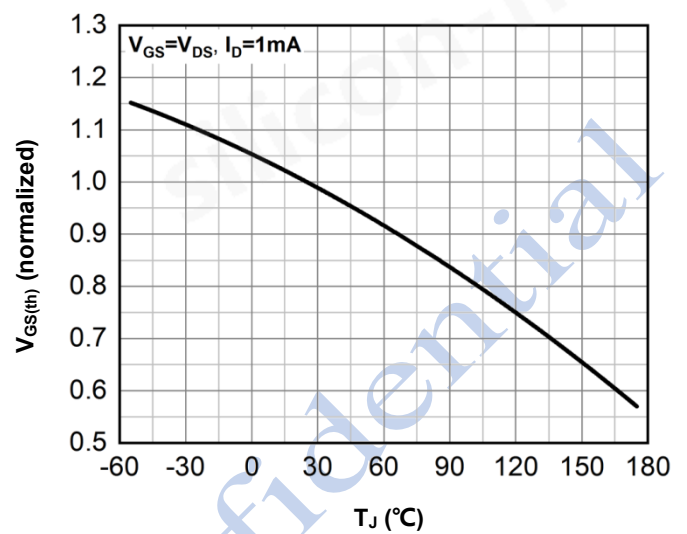
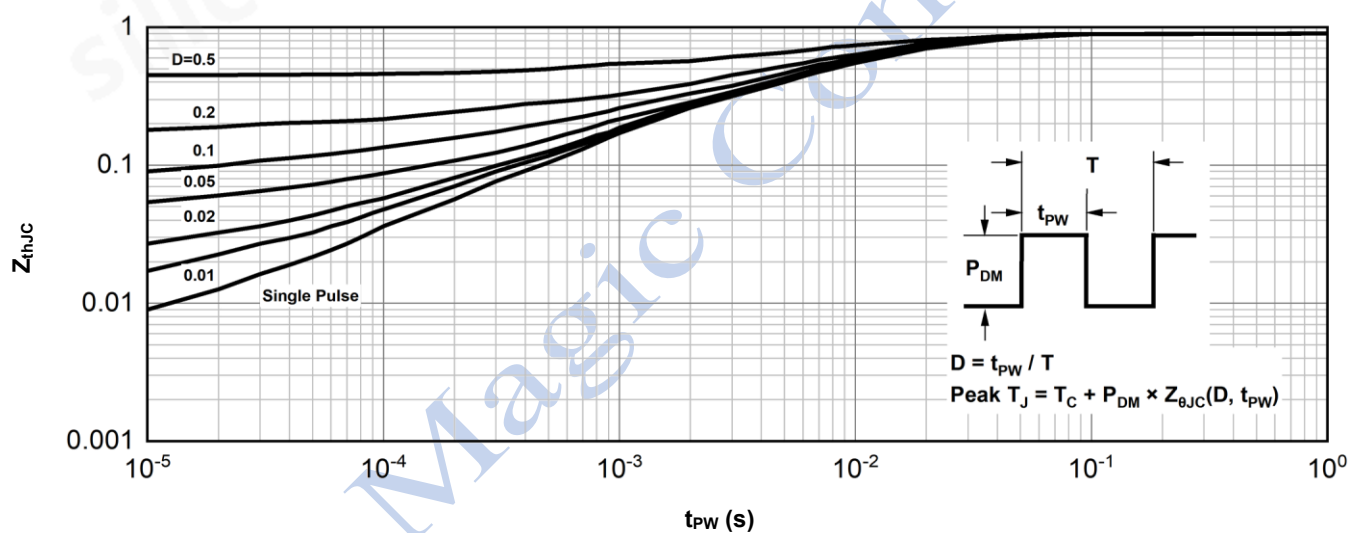
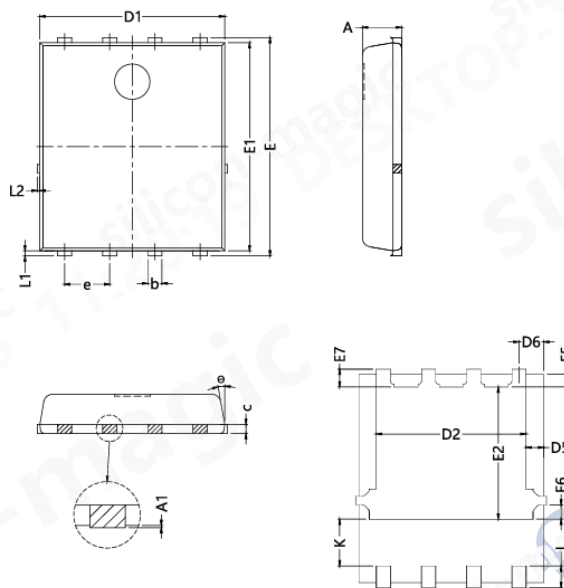


Fig.15 Transient thermal impedance from junction to case



5. Package outline dimensions



Dim	Millimeters		
	Min	Nom	Max
A	1.00	1.10	1.20
A1	0.00	—	0.05
b	0.30	0.40	0.50
c	0.20	0.25	0.30
D1	5.10	5.20	5.30
D2	4.06	4.21	4.36
D3	3.69	3.84	3.99
D4	2.45	2.60	2.75
D5	0.35	0.5	0.65
D6	0.55	0.70	0.85
E	6.00	6.15	6.30
E1	5.76	5.86	5.96
E2	3.57	3.72	3.87
E3	3.67	3.82	3.97
E4	2.24	2.39	2.54
E5	0.21	0.36	0.51
E6	0.25	0.40	0.55
E7	0.35	0.50	0.65
e	1.27 BSC		
L	0.50	0.61	0.71
L1	0.05	0.15	0.25
L2	0.02	0.08	0.15
K	1.10	—	—
ø	8°	10°	12°

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